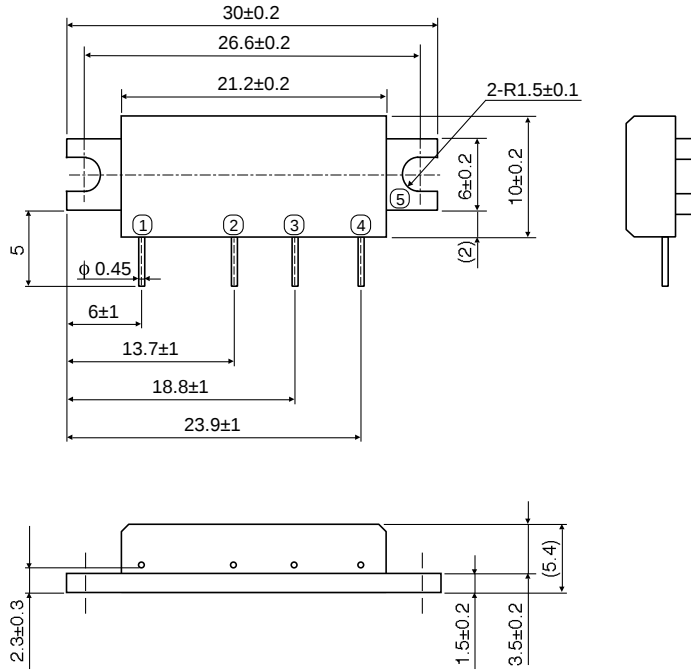


SILICON MOS FET POWER AMPLIFIER, 490-512MHz, 7W, FM PORTABLE RADIO

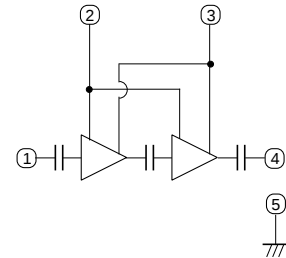
OUTLINE DRAWING

Dimensions in mm



H46

BLOCK DIAGRAM



PIN:

- ①Pin : RF INPUT
- ②V_{GG} : GATE BIAS SUPPLY
- ③V_{DD} : DRAIN BIAS SUPPLY
- ④P_O : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DD}	Supply voltage	V _{GG} ≤3.5V, Z _G =Z _L =50Ω	9.2	V
V _{GG}	Gate bias voltage		4	V
P _{in}	Input power	f=490-512MHz, Z _G =Z _L =50Ω	70	mW
P _O	Output power	f=490-512MHz, Z _G =Z _L =50Ω	10	W
T _C (OP)	Operation case temperature	f=490-512MHz, Z _G =Z _L =50Ω	-30 to +100	°C
T _{stg}	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (T_C=25°C, Z_G=Z_L=50Ω unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		490	512	MHz
P _O	Output power	V _{DD} =7.2V, V _{GG} =3.5V, P _{in} =50mW	7		W
η _T	Total efficiency		40		%
2f _o	2nd. harmonic			-25	dBc
ρ _{in}	Input VSWR			4	-
-	Stability	Z _G =50Ω, V _{DD} =4-9.2V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	V _{DD} =9.2V, P _{in} =50mW, P _O =7W (V _{GG} adjust), Z _L =20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 490-512MHz, 7W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA

